

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Taketomi ASAMI et al.

Serial No. 09/842,315

Filed: 04/26/2001

For: MANUFACTURING METHOD FOR
SEMICONDUCTOR DEVICE



Group Art Unit: 2813

Examiner: David S. Blum

Confirmation No. 5664

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope address to: Commissioner for Patents, Washington, D.C. 20231, on May 17, 2002.

Ava M. Dixon

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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed January 17, 2002, please amend the above identified application as follows.

IN THE CLAIMS:

Please amend claims 1-14 as follows:

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1. (Amended) A method for manufacturing a semiconductor device comprising:
- the first step of forming a semiconductor film;
 - the second step of etching the semiconductor film to remove contaminant impurities on a surface of said semiconductor film; and
 - the third step of forming a gate insulating film in contact with said semiconductor film after said second step;

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